



**Solid State Devices, Inc.**

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 Phone: (562) 404-4474 \* Fax: (562) 404-1773  
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**SFT22907GW  
Series**

**Dual Microminiature Package  
600 mA 60 Volts  
Complimentary NPN & PNP  
Transistor**

- Features:**
- High Speed Switching Transistor
  - Multiple Devices Reduce Board Space
  - High Power Dissipation: Up to 1.2 W / device
  - TX, TXV, S-Level screening available
  - Replaces both 2N2222AU & 2N2907AU

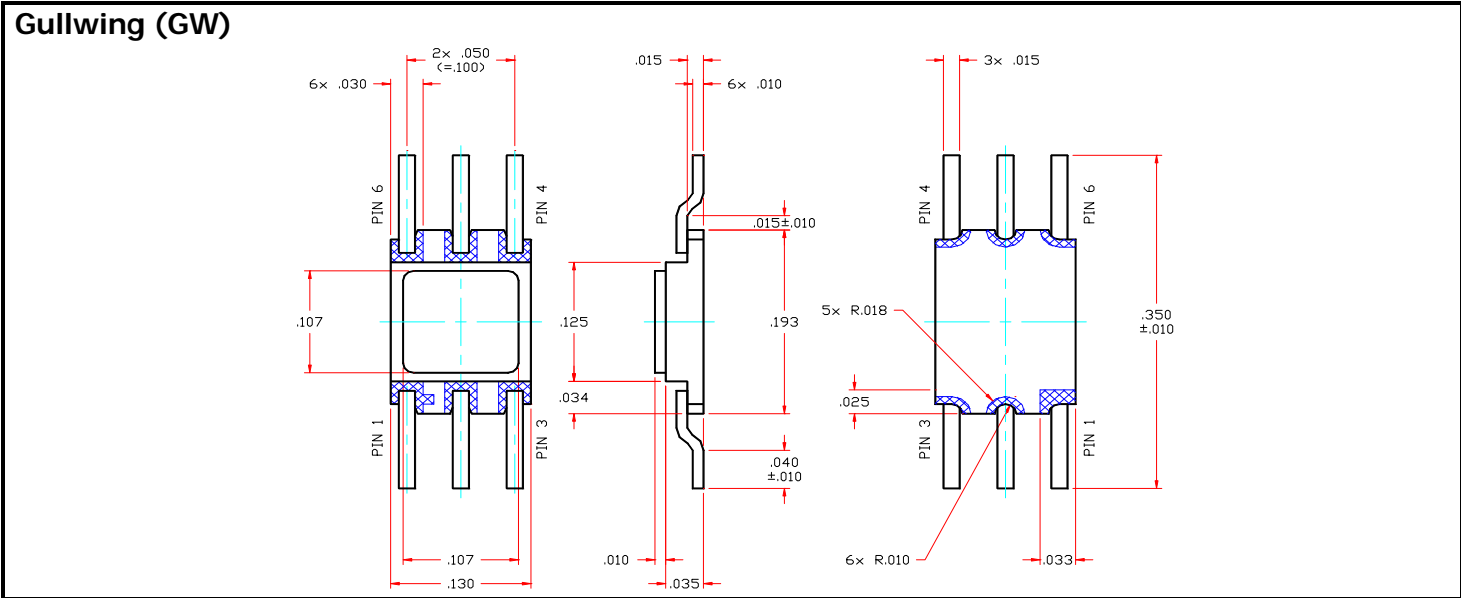
**DESIGNER'S DATA SHEET**

**Part Number / Ordering Information**<sup>1/</sup>

SFT22907 **GW**  Screening<sup>2/</sup> = Commercial  
 TX = TX Level  
 TXV = TXV Level  
 S = S Level

Package GW = Gullwing

Maximum Ratings	Symbol	2N2222 NPN	2N2907 PNP	Units
Collector – Emitter Voltage	$V_{CEO}$	50	60	Volts
Collector – Base Voltage	$V_{CBO}$	75	60	Volts
Emitter – Base Voltage	$V_{EBO}$	6	5	Volts
Continues Collector Current	$I_C$	800	600	mAmps
Power Dissipation @ $T_A = 25^\circ C$ Per device	$P_D$	500	500	mW
Power Dissipation @ $T_A = 25^\circ C$ Total		660		
Operating & Storage Temperature	$T_{op}$ & $T_{stg}$	-65 to +200	-65 to +200	$^\circ C$
Maximum Thermal Resistance Junction to PCB	$R_{OJ-PCB}$	245	245	$^\circ C/W$



**NOTE:** All specifications are subject to change without notification. SCD's for these devices should be reviewed by SSDI prior to release.

**DATA SHEET #: TR0032F**



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Electrical Characteristics <sup>4/</sup>	Symbol	NPN Bias	Limit	PNP Bias	Limit
Collector – Emitter Sustaining Voltage	$BV_{CEO}$	$I_C = 10 \text{ mA}$	50V	$I_C = 10 \text{ mA}$	60V
Collector Cutoff Current	$I_{CES}$	$V_{CE} = 50 \text{ V}$	50 nA max	$V_{CE} = 50 \text{ V}$	50 nA max
Collector Cutoff Current	$I_{CBO}$	$V_{CB} = 60 \text{ V}$ $V_{CB} = 75 \text{ V}$ $V_{CB} = 60 \text{ V}, T_A = 150^\circ\text{C}$	10 nA max 10 $\mu\text{A}$ max 10 $\mu\text{A}$ max	$V_{CB} = 50 \text{ V}$ $V_{CB} = 60 \text{ V}$ $V_{CB} = 50 \text{ V}, T_A = 150^\circ\text{C}$	10 nA max 10 $\mu\text{A}$ max 10 $\mu\text{A}$ max
Emitter Cutoff Current	$I_{EBO}$	$V_{EB} = 4 \text{ V}$ $V_{EB} = 6 \text{ V}$	10 nA max 10 $\mu\text{A}$ max	$V_{EB} = 4 \text{ V}$ $V_{EB} = 5 \text{ V}$	50 nA max 10 $\mu\text{A}$ max
DC Current Forward Transfer Ratio *	$h_{FE}$	$I_C = 0.1 \text{ mA}, V_{CE} = 10 \text{ V}$ $I_C = 1.0 \text{ mA}, V_{CE} = 10 \text{ V}$ $I_C = 10 \text{ mA}, V_{CE} = 10 \text{ V}$ $I_C = 150 \text{ mA}, V_{CE} = 10 \text{ V}$ $I_C = 500 \text{ mA}, V_{CE} = 10 \text{ V}$	50 min 75 - 325 100 min 100 - 300 30 min	$I_C = 100 \mu\text{A}, V_{CE} = 10 \text{ V}$ $I_C = 1 \text{ mA}, V_{CE} = 10 \text{ V}$ $I_C = 10 \text{ mA}, V_{CE} = 10 \text{ V}$ $I_C = 150 \text{ mA}, V_{CE} = 10 \text{ V}$ $I_C = 500 \text{ mA}, V_{CE} = 10 \text{ V}$	75 min 100 - 450 100 min 100 - 300 50 min
DC Current Forward Transfer Ratio *	$h_{FE}$	$I_C = 10 \text{ mA}, V_{CE} = 10 \text{ V}$ $T_A = -55^\circ\text{C}$	35 min	$I_C = 10 \text{ mA}, V_{CE} = 10 \text{ V}$ $T_A = -55^\circ\text{C}$	50 min
Small Signal Current Gain ( $f = 1 \text{ kHz}$ )	$h_{fe}$	$I_C = 1.0 \text{ mA}, V_{CE} = 10 \text{ V}$	50 - 300	—	—
Collector-Emitter Saturation Voltage *	$V_{CE(SAT)}$	$I_C = 150 \text{ mA}, I_B = 15 \text{ mA}$ $I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$	0.3V max 1.0V max	$I_C = 150 \text{ mA}, I_B = 15 \text{ mA}$ $I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$	0.4 V max 1.6 V max
Base-Emitter Saturation Voltage *	$V_{BE(SAT)}$	$I_C = 150 \text{ mA}, I_B = 15 \text{ mA}$ $I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$	0.6 – 1.2V 2.0V max	$I_C = 150 \text{ mA}, I_B = 15 \text{ mA}$ $I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$	0.6 - 1.3 V 2.6 V max
Frequency Transition (Small signal current gain) @ $f = 100\text{MHz}$	$f_T$	$V_{CE} = 20 \text{ V}, I_C = 20 \text{ mA},$ $f = 100 \text{ MHz}$	250 MHz min	$V_{CE} = 20 \text{ V}, I_C = 20 \text{ mA},$ $f = 100 \text{ MHz}$	200 MHz min
Output Capacitance	$C_{ob}$	$V_{CB} = 10 \text{ V}, f = 1 \text{ MHz}$	8.0 pF max	$V_{CB} = 10 \text{ V}, f = 1.0 \text{ MHz}$	8.0 pF max
Input Capacitance	$C_{ib}$	$V_{EB} = 0.5 \text{ V}, f = 1 \text{ MHz}$	25 pF max	$V_{BE} = 2.0 \text{ V}, f = 1.0 \text{ MHz}$	30 pF max
Switching Times	$t_{(on)}$	$V_{cc} = -30 \text{ V}, I_C = 150 \text{ mA}, I_{B1}$ $= I_{B2} = 15 \text{ mA}, V_{BE(off)} = 3\text{V}$	35 ns max	$V_{cc} = -30 \text{ V}, I_C = 150 \text{ mA}, I_{B1}$ $= I_{B2} = 15 \text{ mA}, V_{BE(off)} = 3\text{V}$	45 ns max
	$t_{(off)}$	$V_{cc} = -30 \text{ V}, I_C = 150 \text{ mA}, I_{B1}$ $= I_{B2} = 15 \text{ mA}, V_{BE(off)} = 3\text{V}$	300 ns max	$V_{cc} = -30 \text{ V}, I_C = 150 \text{ mA}, I_{B1}$ $= I_{B2} = 15 \text{ mA}, V_{BE(off)} = 3\text{V}$	300 ns max

**NOTES:**  
 \* Pulse Test: Pulse Width = 300 $\mu\text{sec}$ , Duty Cycle = 2%  
 1/ For Ordering Information, Price, and Availability Contact Factory.  
 2/ Screening per MIL-PRF-19500  
 3/ For Package Outlines Contact Factory.  
 4/ Unless Otherwise Specified, All Electrical Characteristics @25°C.

Available Part Numbers: SFT22907GW	PIN ASSIGNMENT						
	Package	Pin 1	Pin 2	Pin 3	Pin 4	Pin 5	Pin 6
	GW	Collector SFT2222	Base SFT2222	Emitter SFT2222	Collector SFT2907	Base SFT2907	Emitter SFT2907